(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
29 May 2008 (29.05.2008)

PCT

(10) International Publication Number
WO 2008/062934 A1

(51) International Patent Classification:
H01L 31/042 (2006.01)

(21) International Application Number:
PCT/KR2007/002976

(22) International Filing Date: 20 June 2007 (20.06.2007)

(25) Filing Language: Korean

(26) Publication Language: English

(30) Priority Data:
10-2006-0114282
20 November 2006 (20.11.2006) KR

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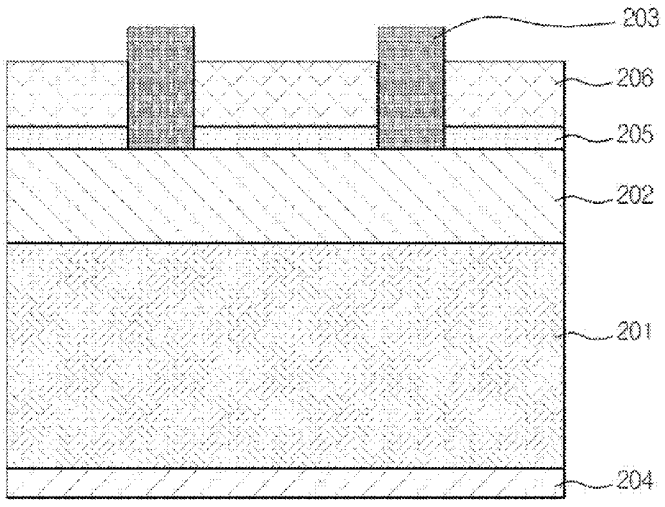
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

(54) **Title:** SOLAR CELL AND METHOD FOR MANUFACTURING THE SAME



(57) **Abstract:** A solar cell includes a p-n structure having a first conductive semiconductor substrate, a second conductive semiconductor layer formed on the first conductive semiconductor substrate and having a conduction opposite to the first conductive semiconductor substrate, and a p-n junction formed at an interface between the first and second conductive semiconductor substrate/layer; a first anti-reflection film formed on the second conductive semiconductor layer and composed of SiNx:H thin film with 40-100 nm thickness; a second anti-reflection film formed on the first anti-reflection film and composed of silicon oxy-nitride; a front electrode formed on the second anti-reflection film in a predetermined pattern and connected to the second conductive semiconductor layer through the first and second anti-reflection films; and a rear electrode formed at an opposite side to the front electrode with the first conductive semiconductor substrate being interposed therebetween to be connected to the first conductive semiconductor substrate.

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Description

SOLAR CELL AND METHOD FOR MANUFACTURING THE SAME

Technical Field

[1] The present invention relates to a solar cell and its manufacturing method, and more particularly to a solar cell having an improved anti-reflection film structure to give excellent photoelectric conversion efficiency and a method for manufacturing the same.

Background Art

[2] Recently, as exhaustion of existing energy resources such as petroleum and coal is estimated, interests on alternative energies for substituting them are more increased. Among the alternative energies, a solar cell is particularly spotlighted since its energy resource is sufficient and it does not cause any environmental pollution. A solar cell is classified into a solar heat cell that generates a vapor required for rotating a turbine using a solar heat, and a solar light cell that converts photons into electric energy using the properties of a semiconductor. Generally, a solar cell calls the solar light cell (hereinafter, the term 'solar cell' is used).

[3] Referring to FIG. 1 showing a basic structure of a solar cell, the solar cell has a junction structure of a p-type semiconductor 101 and a n-type semiconductor 102 like a diode. If photons are input to the solar cell, the photons are reacted with materials of the semiconductor to generate electrons of (-) charge and holes of (+) charge caused by removal of the electrons, thereby allowing flow of electric current as they are moving. It is called photovoltaic effect. Among the p-type semiconductor 101 and the n-type semiconductor 102 that composes the solar cell, electrons are drawn toward the n-type semiconductor 102 and the holes are drawn toward the p-type semiconductor 101, so they are moved to electrodes 103, 104 joined to the n-type semiconductor 101 and the p-type semiconductor 102, respectively. If the electrodes 103, 104 are connected using a cable, it is possible to obtain an electric power as electricity flows.

[4] Such output features of a solar cell are generally evaluated by measuring an output current-voltage curve using a solar simulator. On the curve, a point at which a multiplication $Ip \times Vp$ of an output current Ip and an output voltage Vp is maximum is called a maximum output Pm. Also, a value obtained by dividing Pm by a total optical energy ($S \times I$: S is an area of an element, I is an intensity of light irradiated to the solar cell) input to the solar cell is defined as conversion efficiency η.

[5] The efficiency η of the solar cell is determined by a short-circuit current Jsc (an output current at V=0 on the current-voltage curve), an open voltage Voc (an output

voltage at I=0 on the current-voltage curve), and FF (fill factor) indicating how the output current-voltage curve is close to a square shape. Here, as FF has a value close to 1 (100%), the output current-voltage curve approximates to an ideal square shape, and the conversion efficiency h is increased.

[6] In order to enhance the efficiency of a solar cell, it is required to increase Jsc or Voc, and makes FF (fill factor) approximate to 1 (100%). Jsc is generally increased when reflectance to the light irradiated to the solar cell is reduced, Voc is increased when the degree of recombination of carriers (electrons and holes) is reduced, and FF approximates to 1 (100%) when a resistance in the n-type and p-type semiconductors and between the semiconductors and electrodes is decreased. In this point, it would be understood that Jsc, Voc and FF, which are factors for determining the efficiency of a solar cell, are controlled by different factors.

[7] Conventionally, reflectance of light input to a receiving side of the solar cell was decreased to increase Jsc and thus enhance efficiency of the solar cell. In order to reduce reflectance of light, there are used a method of forming an anti-reflection film to the receiving side of the solar cell to reduce reflectance of light, and a method of minimizing an area hiding photons when forming an electrode terminal in order to reduce reflectance of light. Among them, various studies on the anti-reflection film capable of realizing a low reflectance are under progress.

[8] Recently, a method of forming an anti-reflection film composed of a silicon nitride film on an emitter at a front surface of a solar cell to reduce reflectance is developed and widely used. As an example, Korean Laid-open Patent Publication No. 2003-0079265 (hereinafter, referred to as 'a first conventional method') discloses a method of improving performance of a solar cell using a dual anti-reflection structure in which an amorphous silicon thin film and a silicon nitride film are subsequently laminated. However, the amorphous silicon thin film may attribute to increase of Voc to some extent by defect passivation of the surface of the solar cell, but it cannot cause any meaningful effect for the silicon nitride film in aspect of the reduction of reflectance that is an inherent function of the anti-reflection film. That is to say, between two factors Voc and Jsc that determines efficiency of a solar cell, the first conventional method adopts a mechanism that increases efficiency of a solar cell just by increasing Voc mainly. Thus, the first conventional method has a limit that it does not improve efficiency of a solar cell in various aspects.

[9] As another example, US 4,649,088 (hereinafter, referred to as 'a second conventional method') discloses a method of forming an anti-reflection film by sputtering using silicon or silicon oxide film as a target to a receiving side of a solar cell, in which the anti-reflection film has a refractive index continuously reduced from the surface of the silicon substrate to the air, and the anti-reflection film has material constitutions

continuously changing in the order of silicon nitride film -> silicon oxy-nitride film -> silicon oxide film so as to lower reflectance of light. The second conventional method discloses that efficiency of a solar cell may be improved by lowering reflectance of light using the anti-reflection film having the above features. However, the second conventional method fails to teach any passivation of the silicon substrate, which is another factor giving an influence on the efficiency of a solar cell. The second conventional method forms the anti-reflection film by means of sputtering, but it strongly supports the fact that the second conventional method does not have any intention to improve efficiency of a solar cell using passivation of the silicon substrate surface. If sputtering is used for forming an insulation film using silicon, it is substantially impossible to passivate the surface of a silicon substrate due to bad interface features of the insulation film. Thus, the second conventional method is considered to adopt the mechanism of improving efficiency of a solar cell by mainly increasing Jsc between two factors Voc and Jsc that determines efficiency of a solar cell. As a result, the second conventional method is similar to the first convention method in the point that it does not improve efficiency of a solar cell in various aspects.

Disclosure of Invention

Technical Problem

[10] The present invention is designed to solve the problems of the prior art, and therefore it is an object of the present invention to provide a solar cell having a new anti-reflection film structure capable of increasing efficiency of the solar cell in various aspects by conducting a passivation function on a substrate surface of the solar cell and a function of reducing reflectance of light at the same time.

[11] Recently, a SiNx:H thin film grown by PECVD (Plasma Enhanced Chemical Vapor Deposition) is spotlighted as a material that can be used as an anti-reflection film of a solar cell. Here, the SiNx:H thin film means a silicon nitride film containing a large amount of hydrogen atoms, grown by PECVD under a hydrogen environment.

[12] The anti-reflection film composed of the SiNx:H thin film is advantageously capable of playing a function of reducing reflectance of light incident onto the solar cell and a function of passivating defects on a surface of the silicon substrate by diffusion of hydrogen atoms contained in the SiNx:H thin film at the same time. In order to maximize dual functions of the anti-reflection film, it is required to precisely control refractive index and thickness of the SiNx:H thin film. Here, the refractive index of the thin film has a relatively close relation with the reduction of reflectance, while the thickness of the thin film has a relatively close relation with the passivation of the surface of the silicon substrate.

[13] However, the inventor found that the technique of forming an anti-reflection film

using the SiNx:H thin film has the following drawbacks. That is, an optimal refractive index and an optimal thickness of the SiNx:H thin film capable of minimizing reflectance of light are not identical to an optimal refractive index and an optimal thickness of the SiNx:H thin film capable of maximizing passivation of the surface of the silicon substrate. Thus, if the anti-reflection film is composed of SiNx:H thin film in one layer, it would be impossible to accomplish both functions, namely passivation of the surface of the silicon substrate and reduction of reflectance.

Technical Solution

[14] In order to overcome such a limitation, the inventor formed a SiNx:H thin film on a silicon substrate of a solar cell by PECVD, then formed various silicon insulation films in-situ thereon, and then analyzed Voc and Jsc of the solar cell. As a result, it was checked that both functions of the SiNx:H thin film may be realized to the maximum when a silicon oxy-nitride film was formed on the SiNx:H thin film, and also it was possible to obtain refractive index and thickness ranges of the SiNx:H thin film that allows to maximize passivation of a silicon substrate and reduction of reflectance.

[15] More specifically, in order to accomplish the above object, there is provided a solar cell, which includes a p-n structure having a first conductive semiconductor substrate, a second conductive semiconductor layer formed on the first conductive semiconductor substrate and having a conduction opposite to the first conductive semiconductor substrate, and a p-n junction formed at an interface between the first conductive semiconductor substrate and the second conductive semiconductor layer; a first anti-reflection film formed on the second conductive semiconductor layer and composed of SiNx:H thin film with a thickness of 40 nm to 100 nm; a second anti-reflection film formed on the first anti-reflection film and composed of silicon oxy-nitride; a front electrode formed on the second anti-reflection film according to a predetermined pattern and connected to the second conductive semiconductor layer through the first and second anti-reflection films; and a rear electrode formed at an opposite side to the front electrode with the first conductive semiconductor substrate being interposed therebetween so as to be connected to the first conductive semiconductor substrate.

[16] In another aspect of the present invention, there is also provided a method for manufacturing a solar cell, which includes (S1) forming on a first conductive semiconductor substrate a second conductive semiconductor layer having an opposite conduction thereto to form a p-n junction at an interface thereof; (S2) forming a first anti-reflection film composed of SiNx:H thin film with a thickness of 40 nm to 100 nm on the second conductive semiconductor layer; (S3) forming a second anti-reflection film composed of silicon oxy-nitride on the first anti-reflection film; (S4) forming a front electrode on the second anti-reflection film so as to be connected to the second

conductive semiconductor layer; and (S5) forming a rear electrode at an opposite side to the front electrode with the first conductive semiconductor substrate being interposed therebetween so as to be connected to the first conductive semiconductor substrate.

[17] Preferably, the first anti-reflection film has a refractive index of 1.5 to 3.4.

[18] Preferably, the second anti-reflection film has a thickness of 10 nm to 200 nm and a refractive index of 1.45 to 2.4.

[19] Preferably, the first and second anti-reflection films have discontinuous refractive indexes at a border interface.

[20] Preferably, the first and second anti-reflection films are formed using an in-situ process by PECVD.

[21] Preferably, the front electrode is formed in a way of coating a front electrode-forming paste on the second anti-reflection film into a predetermined pattern and then thermally treating the coated paste. Also, the rear electrode is preferably formed in a way of coating a rear electrode-forming paste on the first conductive semiconductor substrate into a predetermined pattern and then thermally treating the coated paste.

[22] In the present invention, the first conductive semiconductor substrate is a p-type silicon substrate, and the second conductive semiconductor layer is a n-type emitter layer, or vice versa. A doping layer containing high density impurities (for example a p+ layer) acting as BSF (Back Surface Field) may be formed at an interface between the first conductive semiconductor substrate and the rear electrode.

Brief Description of the Drawings

[23] Other objects and aspects of the present invention will become apparent from the following description of embodiments with reference to the accompanying drawing in which:

[24] FIG. 1 is a schematic view showing a basic structure of a solar cell; and

[25] FIG. 2 is a schematic view showing a solar cell according to one embodiment of the present invention.

Best Mode for Carrying Out the Invention

[26] Hereinafter, a preferred embodiment of the present invention will be explained with reference to the accompanying drawing.

[27] FIG. 2 is a schematic sectional view showing a solar cell according to one embodiment of the present invention. As shown in FIG. 2, the solar cell of the present invention includes a p-n structure, a first anti-reflection film 205, a second anti-reflection film 206, a front electrode 203 and a rear electrode 204.

[28] The p-n structure includes a first conductive semiconductor substrate 201, a second conductive semiconductor layer 202 formed on the first conductive semiconductor

substrate 201 and having an opposite conduction to the first conductive semiconductor substrate 201, and a p-n junction formed at an interface between the first conductive semiconductor substrate 201 and the second conductive semiconductor layer 202. The p-n structure receives light to generate current by means of photoelectromotive force. Representatively, the first conductive semiconductor substrate 201 is a p-type silicon substrate doped with Group 3 element such as B, Ga and In, and the second conductive semiconductor layer 202 is a n-type emitter layer doped with Group 5 element such as P, As and Sb. The p-n junction is formed by joining the p-type silicon substrate and the n-type emitter layer. As an alternative, the p-n junction may also be formed by laminating a p-type emitter layer on a n-type silicon substrate. However, the p-n structure of the present invention is not limited thereto.

[29] On the second conductive semiconductor layer 202 having the p-n structure, the first anti-reflection film 205 composed of SiNx:H thin film and the second anti-reflection film 206 composed of silicon oxy-nitride film are subsequently formed. That is to say, the first anti-reflection film 205 is formed on the second conductive semiconductor layer 202, and the second anti-reflection film 206 is formed on the first anti-reflection film 205.

[30] The first anti-reflection film 205 functions to passivate defects such as dangling bond existing in bulks or surface of a silicon substrate and also to reduce reflectance of light incident onto a front surface of the silicon substrate, thereby enhancing a photoelectric conversion efficiency of photons. If the defect of the silicon substrate is passivated, a recombination site of minority carrier is removed to increase Voc. Also, if the reflectance of light is decreased, an amount of light reaching the p-n junction is increased to increase Jsc. As a result, the efficiency of solar cell is improved as much as the increased amounts of Voc and Jsc.

[31] The silicon substrate is passivated by means of hydrogen atoms included in the SiNx:H thin film that composes the first anti-reflection film 205. That is to say, hydrogen atoms are diffused toward the silicon substrate while or after the first anti-reflection film 205 is formed or during the followed thermal treatment process, thereby passivating defects in the substrate of the silicon substrate or bulks adjacent to the surface.

[32] The second anti-reflection film 206 further reduces reflectance of light incident onto a front surface of the silicon substrate in combination with the first anti-reflection film 205. Furthermore, the second anti-reflection film 206 optimizes a refractive index range and a film thickness range of the first anti-reflection film 205 such that dual functions (passivation and reflectance reduction) of the first anti-reflection film 205 may be maximized. That is to say, when being composed only of SiNx:H thin film, the second anti-reflection film 206 solves mutual discordance between refractive index and

film thickness for optimizing passivation of the silicon substrate and refractive index and thickness for minimizing reflectance of light. Accordingly, it becomes possible to suitably tune the refractive index range and the film thickness range capable of realizing dual functions of the first anti-reflection film 205.

[33] Preferably, the first anti-reflection film 205 has a refractive index of 1.5 to 3.4 and a film thickness of 40 nm to 100 nm. If the first anti-reflection film 205 is formed under the above conditions, the dual functions of the first anti-reflection film 205 may be maximized. That is to say, due to the presence of the second anti-reflection film 206, it is possible to tune a refractive index range and a film thickness range capable of maximizing dual functions of the first anti-reflection film 205.

[34] In relation to the numerical range for the refractive index of the first anti-reflection film 205, a refractive index less than the lower limit causes more reflection, so the first anti-reflection film 205 cannot act as an anti-reflection film. In addition, since passivation of the silicon substrate is deteriorated, the efficiency of solar cell is also deteriorated. In addition, if a refractive index exceeds the upper limit, the photoelectric efficiency is deteriorated due to the absorption of the anti-reflection film itself, undesirably. Also, in relation to the numerical range for the thickness of the first anti-reflection film 205, a thickness less than the lower limit makes the first anti-reflection film 205 unsuitable for acting as an anti-reflection film. Also, if a thickness exceeds the upper limit, light is absorbed in the anti-reflection film itself, undesirably.

[35] Preferably, the second anti-reflection film 206 has a refractive index of 1.45 to 2.4. The refractive index of the second anti-reflection film 206 is smaller than the refractive index of the first anti-reflection film 205, but preferably the refractive index of the second anti-reflection film 206 is discontinuously decreased at a border interface based on the first anti-reflection film 205. In relation to the numerical range for the refractive index of the second anti-reflection film 206, if a refractive index is less than the lower limit, the second anti-reflection film 206 cannot be realized using silicon oxy-nitride. If a refractive index exceeds the upper limit, the photoelectric conversion efficiency is rather deteriorated due to an increased absorption of the anti-reflection film itself, undesirably.

[36] Preferably, the second anti-reflection film 206 has a thickness of 10 nm to 200 nm. In relation to the numerical range for the thickness of the second anti-reflection film 206, if a thickness is less than the lower limit, the second anti-reflection film 206 becomes insufficient for acting as an anti-reflection film. If a thickness exceeds the upper limit, light is absorbed in the anti-reflection film itself, undesirably.

[37] The first anti-reflection film 205 is formed by means of deposition that may include a large amount of hydrogen atoms in a silicon nitride film. Preferably, the first anti-reflection film 205 is formed using chemical deposition capable of making a hydrogen

environment, more preferably using PECVD. The second anti-reflection film 206 is formed in the same way as the first anti-reflection film 205. Preferably, the first anti-reflection film 205 and the second anti-reflection film 206 are formed by means of the in-situ process using the same deposition chamber.

[38] The front electrode 203 is formed on the first and second anti-reflection films 205, 206 in a predetermined pattern, and the front electrode 203 is connected to the second conductive semiconductor layer 202 through the first and second anti-reflection films 205, 206. In addition, the rear electrode 204 is formed at an opposite side to the front electrode 203 with the anti-reflection films 205, 206 and the first conductive semiconductor substrate 201 being interposed therebetween, so as to be connected to the first conductive semiconductor substrate 201. If loads are applied to these electrodes 203, 204, electricity generated in the solar cell can be utilized. The front electrode 203 representatively employs a silver electrode since the silver electrode has an excellent electric conductivity. Also, the rear electrode 204 representatively employs an aluminum electrode since the aluminum electrode has an excellent conductivity and allows well junction due to good affinity with silicon. In addition, the aluminum electrode corresponds to Group 3 element, which forms a p+ layer, namely BSF (Back Surface Field), at a contact surface with the silicon substrate such that carriers are not disappeared but collected, thereby enhancing efficiency of the solar cell.

[39] The present invention also provides a method for manufacturing the solar cell explained above.

[40] According to the method for manufacturing a solar cell of the present invention, first, on the first conductive semiconductor substrate 201, the second conductive semiconductor layer 202 having an opposite conduction thereto is formed such that a p-n junction is formed at their interface. A p-type silicon substrate is representatively used as the first conductive semiconductor substrate 201. For example, a p-type silicon substrate is coated with a n-type dopant and then thermally treated such that the n-type dopant is diffused to the p-type silicon substrate, thereby forming the p-n junction. On the contrary, it is also possible to diffuse a p-type dopant on a n-type silicon substrate to form a p-n junction.

[41] Then, the first anti-reflection film 205 composed of SiNx:H thin film is formed on the second conductive semiconductor layer 202. The first anti-reflection film 205 is formed using chemical deposition capable of forming a hydrogen environment, preferably PECVD. Then, the second anti-reflection film 206 composed of silicon oxy-nitride film is formed on the first anti-reflection film 205. The second anti-reflection film 206 is formed in the same chemical deposition as the first anti-reflection film 205, preferably PECVD. The first and second anti-reflection films 205, 206 are preferably formed using the in-situ process in one deposition chamber.

[42] Then, the front electrode 203 connected to the second conductive semiconductor layer 202 is formed on the second anti-reflection film 206, and the rear electrode 204 is formed at an opposite side to the front electrode 203 with the first conductive semiconductor substrate 201 being interposed therebetween, so as to be connected to the first conductive semiconductor substrate 201.

[43] For example, the front electrode 203 and the second electrode 204 may be formed by coating an electrode-forming paste according to a predetermined pattern and then thermally treating it. Due to the thermal treatment, the front electrode 203 punches through the first and second anti-reflection films 205, 206 and connects to the second conductive semiconductor layer 202, and BSF is formed in the rear electrode and the first conductive semiconductor substrate 201. The front electrode 203 and the second electrode 204 may be formed in a reverse order, and also they may be formed by coating paste separately and then thermally treating at the same time.

Mode for the Invention

[44] Hereinafter, the present invention will be explained in more detail using an experimental example. However, it should be understood that the following examples may be modified in various ways, and the scope of the invention should not be limited to the following examples. The following examples are just for better understanding of the present invention to those having ordinary skill in the art.

[45]

[46] Experimental Example 1

[47] A solar cell having a dual anti-reflection film structure as shown in FIG. 2 was prepared. At this time, a p-type polycrystalline silicon substrate (0.5 to 2 Ω) with a size of 125×25 cm^2 was used as a semiconductor substrate, and a n+ emitter layer was formed in 60 Ω/sheet. A first anti-reflection film (refractive index: 2.2, thickness: 55 nm) composed of SiNx:H thin film was formed on the emitter layer using Remote MW Frequency (2.45 GHz) PECVD, and a second anti-reflection film (refractive index: 1.57, thickness: 100 nm) composed of silicon oxy-nitride was formed on the first anti-reflection film using Direct High Frequency (13.56 MHz) PECVD. Deposition temperatures for the first and second anti-reflection films were 400℃ and 350℃, respectively. After that, a silver electrode pattern was printed on the second anti-reflection film by means of screen printing, an aluminum electrode was printed on a side of the semiconductor substrate opposite to the surface where the emitter layer was formed, by means of screen printing, and then they were thermally treated for 30 seconds at 800℃ to form a front electrode and a rear electrode.

[48]

[49] Comparative Example 1

[50] A solar cell having a single anti-reflection film structure composed of SiNx:H thin film was prepared. At this time, a p-type polycrystalline silicon substrate (0.5 to 2 Ω) with a size of 125×25 cm^2 was used as a semiconductor substrate, and a n+ emitter layer was formed in 60 Ω/sheet. An anti-reflection film (refractive index: 2.03, thickness: 75 nm) composed of SiNx:H thin film was formed on the emitter layer using Remote MW Frequency (2.34 GHz) PECVD, in a single layer. Deposition temperature for the anti-reflection film was 400℃. After that, a silver electrode pattern was printed on the anti-reflection film by means of screen printing, an aluminum electrode was printed on a side of the semiconductor substrate opposite to the surface where the emitter layer was formed, by means of screen printing, and then they were thermally treated for 30 seconds at 800℃ to form a front electrode and a rear electrode.

[51]

[52] Comparative Example 2

[53] A solar cell was prepared in the same way as the experimental example 1. However, though the first anti-reflection film composed of SiNx:H and the second anti-reflection film composed of silicon oxy-nitride have the same refractive indexes as them of the experimental example 1, each anti-reflection film has a thickness selected less than a lower limit of the numerical range proposed in the present invention. That is to say, the first anti-reflection film has a thickness of 100 nm, and the second anti-reflection film has a thickness of 30 nm.

[54]

[55] Measurement of Parameters and Efficiency of Solar Cell

[56] Short-circuit current Jsc, open voltage Voc, FF (Fill Factor) and photoelectric conversion efficiency of each solar cell prepared by the experimental example 1 and the comparative examples 1 and 2 were measured using a solar simulator. The measurement results are listed in the following table 1.

[57]

[58] Table 1

	Short-circuit Current (mA)	Open Voltage (mV)	FF (%)	Photoelectric Conversion Efficiency (%)
Experimental Example 1	33.3	619.7	78.2	16.1
Comparative Example 1	32.6	617.5	77.5	15.6
Comparative Example 2	32.1	615.5	75.5	14.0

[59]

[60] Comparing the experimental example 1 with the comparative example 1, it would

be found that Voc, Jsc and FF are all increased to improve photoelectric conversion efficiency in case an anti-reflection film is composed in a dual-layer structure, rather than the case that the anti-reflection film is composed in a single-layer structure. From it, it would be understood that laminating a silicon oxy-nitride film on the SiNx:H thin film may further lower reflectance of light and also give better effect on passivation of a silicon substrate. As a result, the solar cell of the experimental example 1 shows about 0.5% higher efficiency than the solar cell of the comparative example 1.

[61] Meanwhile, based on the single layer, as the SiNx:H thin film is thicker, an amount of hydrogen atoms included in the thin film is increased, so the passivation effect of the silicon substrate is enhanced to increase Voc greater. However, if the thickness of the SiNx:H thin film is increased, there is an adverse effect on the reduction of reflectance. In the solar cell of the comparative example 1, a thickness of the SiNx:H thin film participating in passivation of the silicon substrate is about 5 nm thicker than that of the solar cell of the experimental example 1. However, seeing the table 1, an open voltage Voc of the comparative example 1 is rather smaller than that of the solar cell of the experimental example 1. It supports the fact that, if a silicon oxy-nitride film is formed on the SiNx:H thin film to make the anti-reflection film in a dual layer structure, the laminated silicon oxy-nitride film gives a synergy effect on the passivation of the silicon substrate by the SiNx:H thin film. In addition, if the SiNx:H thin film and the silicon oxy-nitride film are laminated dually, the refractive index range and the film thickness range may be tuned such that the dual functions of the SiNx:H thin film may be all realized. Thus, it would be understood that efficiency of a solar cell is further improved due to the increased Jsc and Voc, compared with the case that the anti-reflection film is formed only using a SiNx:H thin film.

[62] Then, comparing the experimental example 1 with the comparative example 2, if each material layer composing the dual anti-reflection film is not optimized within the numerical range proposed by the present invention, Jsc, Voc and FF are all decreased, though a refractive index of each material layer is identical. In particular, Voc and FF are more decreased than Jsc. From it, it would be understood that, if the first and second anti-reflection films composed of SiNx:H thin film are not formed within the numerical ranges supposed in the present invention, it is impossible to obtain a desired passivation effect of the silicon substrate, and also a resistance characteristic between the electrode and the substrate is deteriorated during an electrode forming process, thereby giving a bad influence on the efficiency of a solar cell. In addition, it would be found again that the refractive index range and the thickness range of the first anti-reflection film composed of SiNx:H thin film are optimal numerical ranges tuned to maximize passivation and reflectance reduction of a silicon substrate by the SiNx:H thin film on the assumption that the second anti-reflection film composed of silicon

oxy-nitride film exists.

[63] It should be understood that the terms used in the specification and the appended claims should not be construed as limited to general and dictionary meanings, but interpreted based on the meanings and concepts corresponding to technical aspects of the present invention on the basis of the principle that the inventor is allowed to define terms appropriately for the best explanation.

[64] Therefore, the description proposed herein is just a preferable example for the purpose of illustrations only, not intended to limit the scope of the invention, so it should be understood that other equivalents and modifications could be made thereto without departing from the spirit and scope of the invention.

Industrial Applicability

[65] The solar cell of the present invention includes a dual anti-reflection film in which a first anti-reflection film made of SiNx:H thin film and a second anti-reflection film made of silicon oxy-nitride are subsequently laminated, so it is possible to realize passivation of a silicon substrate and reduction of reflectance of light at the same time and thus to greatly improve photoelectric conversion efficiency of the solar cell. Also, the SiNx:H thin film and the silicon oxy-nitride film may be continuously formed using an in-site process, which may reduce a manufacture cost.

Claims

[1] A solar cell, comprising:
a p-n structure having a first conductive semiconductor substrate, a second conductive semiconductor layer formed on the first conductive semiconductor substrate and having a conduction opposite to the first conductive semiconductor substrate, and a p-n junction formed at an interface between the first conductive semiconductor substrate and the second conductive semiconductor layer;
a first anti-reflection film formed on the second conductive semiconductor layer and composed of SiNx:H thin film with a thickness of 40 nm to 100 nm;
a second anti-reflection film formed on the first anti-reflection film and composed of silicon oxy-nitride;
a front electrode formed on the second anti-reflection film according to a pre-determined pattern and connected to the second conductive semiconductor layer through the first and second anti-reflection films; and
a rear electrode formed at an opposite side to the front electrode with the first conductive semiconductor substrate being interposed therebetween so as to be connected to the first conductive semiconductor substrate.

[2] The solar cell according to claim 1,
wherein the first anti-reflection film has a refractive index of 1.5 to 3.4.

[3] The solar cell according to claim 1,
wherein the second anti-reflection film has a thickness of 10 nm to 200 nm.

[4] The solar cell according to claim 1,
wherein the second anti-reflection film has a refractive index of 1.45 to 2.4.

[5] The solar cell according to claim 1,
wherein the first and second anti-reflection films have discontinuous refractive indexes at a border interface.

[6] The solar cell according to claim 1,
wherein the first anti-reflection film is formed using CVD (Chemical Vapor Deposition) or PECVD (Plasma Enhanced Chemical Vapor Deposition).

[7] The solar cell according to claim 1,
wherein the second anti-reflection film is formed using CVD or PECVD.

[8] The solar cell according to claim 1,
wherein the first and second anti-reflection films are formed using an in-situ process by PECVD.

[9] The solar cell according to claim 1,
wherein the first conductive semiconductor substrate is a p-type silicon substrate, and the second conductive semiconductor layer is a n-type emitter layer.

[10] The solar cell according to claim 1,
wherein a BSF (Back Surface Field) layer into which high purity impurities are injected is formed at an interface between the first conductive semiconductor substrate and the rear electrode.

[11] A method for manufacturing a solar cell, comprising:
(S1) forming on a first conductive semiconductor substrate a second conductive semiconductor layer having an opposite conduction thereto to form a p-n junction at an interface thereof;
(S2) forming a first anti-reflection film composed of SiNx:H thin film with a thickness of 40 nm to 100 nm on the second conductive semiconductor layer;
(S3) forming a second anti-reflection film composed of silicon oxy-nitride on the first anti-reflection film;
(S4) forming a front electrode on the second anti-reflection film so as to be connected to the second conductive semiconductor layer; and
(S5) forming a rear electrode at an opposite side to the front electrode with the first conductive semiconductor substrate being interposed therebetween so as to be connected to the first conductive semiconductor substrate.

[12] The method for manufacturing a solar cell according to claim 11,
wherein the first anti-reflection film has a refractive index of 1.5 to 3.4.

[13] The method for manufacturing a solar cell according to claim 11,
wherein the second anti-reflection film has a thickness of 10 nm to 200 nm.

[14] The method for manufacturing a solar cell according to claim 11,
wherein the second anti-reflection film has a refractive index of 1.45 to 2.4.

[15] The method for manufacturing a solar cell according to claim 11,
wherein the first and second anti-reflection films have discontinuous refractive indexes at a border interface.

[16] The method for manufacturing a solar cell according to claim 11,
wherein the first anti-reflection film is formed using CVD or PECVD.

[17] The method for manufacturing a solar cell according to claim 11,
wherein the second anti-reflection film is formed using CVD or PECVD.

[18] The method for manufacturing a solar cell according to claim 11,
wherein the first and second anti-reflection films are formed using an in-situ process by PECVD.

[19] The method for manufacturing a solar cell according to claim 11,
wherein the first conductive semiconductor substrate is a p-type silicon substrate, and the second conductive semiconductor layer is a n-type emitter layer.

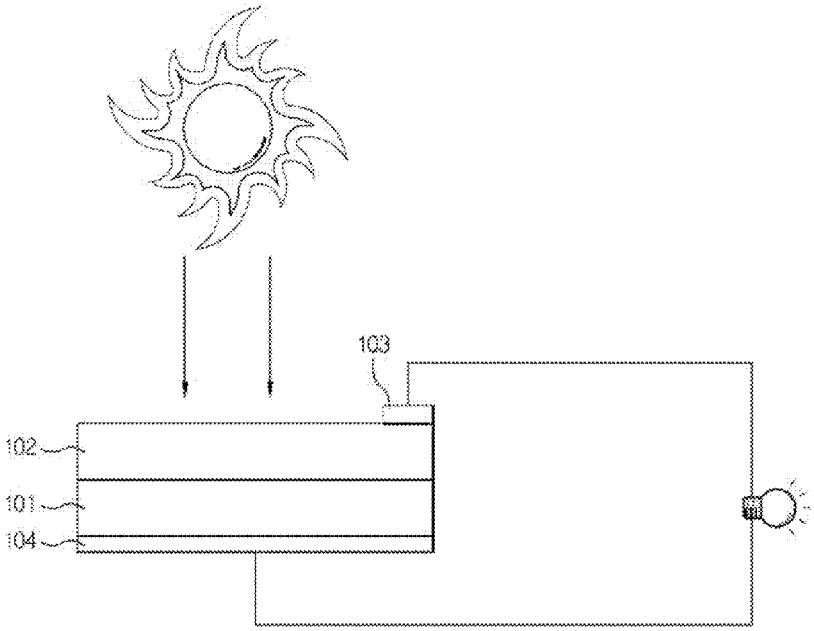
[20] The method for manufacturing a solar cell according to claim 11, further comprising:

forming a BSF layer doped with high purity impurities at an interface between the first conductive semiconductor substrate and the rear electrode.

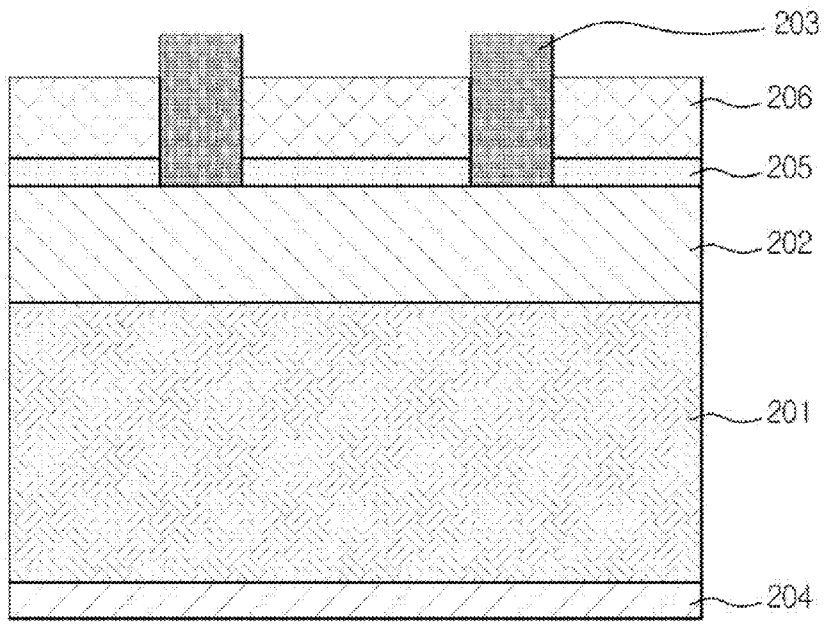
[21] The method for manufacturing a solar cell according to claim 11, wherein, in the step (S4), the front electrode is formed in a way of coating a front electrode-forming paste on the second anti-reflection film into a predetermined pattern and then thermally treating the coated paste.

[22] The method for manufacturing a solar cell according to claim 11, wherein, in the step (S5), the rear electrode is formed in a way of coating a rear electrode-forming paste on the first conductive semiconductor substrate into a predetermined pattern and then thermally treating the coated paste.

[Fig. 1]



[Fig. 2]



INTERNATIONAL SEARCH REPORT

International application No.
PCT/KR2007/002976

A. CLASSIFICATION OF SUBJECT MATTER

H01L 31/042(2006.01)i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC8: H01L 31/042

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean Utility models and applications for Utility models since 1975

Japanese Utility models and applications for Utility models since 1975

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKIPASS(KIPO internal) "solar cell", "antireflection", "thin film"

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 6,825,409 B2 (HAUSSLER, WULF et al.) 30 NOVEMBER 2004 See Claims 1-27 (No Drawings in this document)	1-7, 11-17
Y	US 6,093,882 A (ARIMOTO, SATOSHI) 25 JULY 2000 See Claims 1-9, Figure 8	1-7, 11-17
A	US 6,461,969 B1 (LEE, PEI CHING et al.) 08 OCTOBER 2002 See Claims 1-19, Figure 4	1-22
A	US 6,429,037 B1(WENHAM, STUART ROSS et al.) 01 AUGUST 2002 See Claims 1-22, Figure 4	1-22

☐ Further documents are listed in the continuation of Box C.

☒ See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier application or patent but published on or after the international filing date

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"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents,such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search	Date of mailing of the international search report
12 SEPTEMBER 2007 (12.09.2007)	**12 SEPTEMBER 2007 (12.09.2007)**

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INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

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